74HC366; 74HCT366

Hex buffer/line driver; 3-state; inverting

Rev. 03 — 21 November 2006 Product data sheet

1. General description

The 74HC366; 74HCT366 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC366; 74HCT366 has six inverting buffer/line drivers with 3-state outputs. The 3-state outputs (nY) are controlled by the output enable inputs ($\overline{OE1}$, $\overline{OE2}$). A HIGH on $\overline{OEn}$ causes the outputs to assume a high-impedance OFF-state.

The 74HC366; 74HCT366 is functionally identical to:

- 74HC365; 74HCT365, but has inverted outputs

2. Features

- Inverting outputs
- Complies with JEDEC standard no. 7A
- ESD protection:
  - HBM EIA/JESD22-A114-D exceeds 2000 V
  - MM EIA/JESD22-A115-A exceeds 200 V
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC366				
74HC366D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC366N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil); long body	SOT38-1
74HC366PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT366				
74HCT366D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT366DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT366N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil); long body	SOT38-1
74HCT366PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram

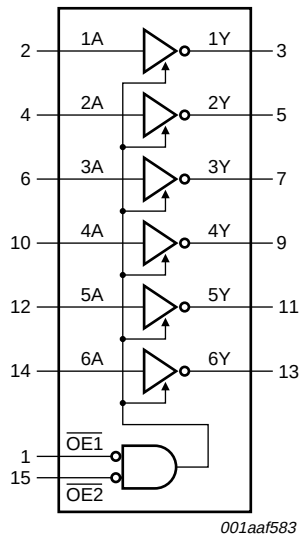


Fig 1. Functional diagram

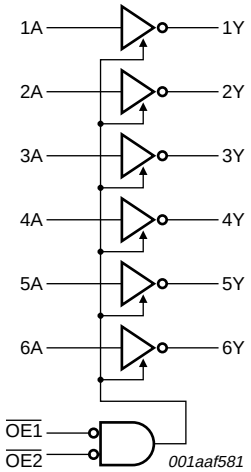


Fig 2. Logic symbol

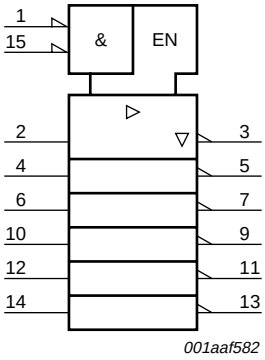


Fig 3. IEC logic symbol

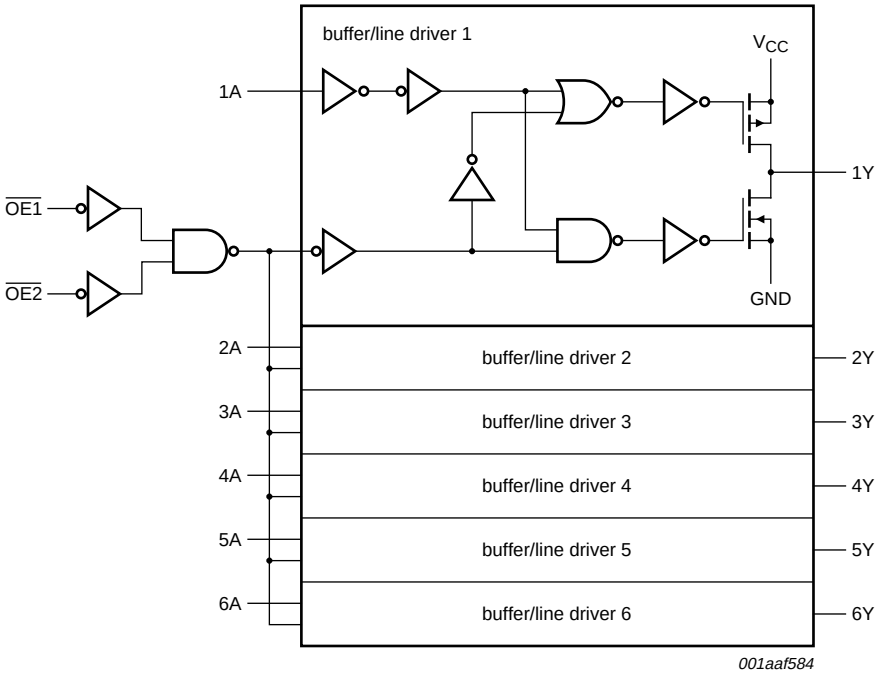


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning

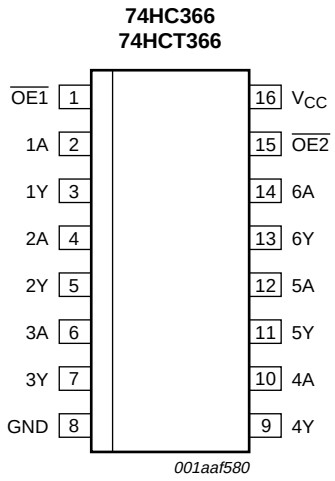


Fig 5. Pin configuration

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{OE1}$	1	output enable input 1 (active LOW)
1A	2	data input 1
1Y	3	data output 1
2A	4	data input 2
2Y	5	data output 2
3A	6	data input 3
3Y	7	data output 3
GND	8	ground (0 V)
4Y	9	data output 4
4A	10	data input 4
5Y	11	data output 5
5A	12	data input 5
6Y	13	data output 6
6A	14	data input 6
$\overline{OE2}$	15	output enable input 2 (active LOW)
V_{CC}	16	supply voltage

6. Functional description

Table 3. Function table[1]

Control		Input	Output
$\overline{OE1}$	$\overline{OE2}$	nA	nY
L	L	L	H
L	L	H	L
X	H	X	Z
H	X	X	Z

[1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7	V
I_{IK}	input clamping current	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±20	mA
I_{OK}	output clamping current	$V_O < –0.5$ V or $V_O > V_{CC} + 0.5$ V		-	±20	mA
I_O	output current	$V_O = –0.5$ V to $(V_{CC} + 0.5$ V)		-	±35	mA
I_{CC}	supply current			-	70	mA
I_{GND}	ground current			-	–70	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	DIP16 package	[1]	-	750	mW
		SO16 package	[2]	-	500	mW
		SSOP16 package	[3]	-	500	mW
		TSSOP16 package	[3]	-	500	mW

[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] For SSOP16 and TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HC366						
V_{CC}	supply voltage		2.0	5.0	6.0	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C

Table 5. Recommended operating conditions *…continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_r	rise time	inputs				
		V_{CC} = 2.0 V	-	-	1000	ns
		V_{CC} = 4.5 V	-	6.0	500	ns
		V_{CC} = 6.0 V	-	-	400	ns
t_f	fall time	inputs				
		V_{CC} = 2.0 V	-	-	1000	ns
		V_{CC} = 4.5 V	-	6.0	500	ns
		V_{CC} = 6.0 V	-	-	400	ns
74HCT366						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C
t_r	rise time	inputs; V_{CC} = 4.5 V	-	6.0	500	ns
t_f	fall time	inputs; V_{CC} = 4.5 V	-	6.0	500	ns

9. Static characteristics

Table 6. Static characteristics 74HC366

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}	-	-	-	
		I_O = –20 µA; V_{CC} = 2.0 V	1.9	2.0	-	V
		I_O = –20 µA; V_{CC} = 4.5 V	4.4	4.5	-	V
		I_O = –20 µA; V_{CC} = 6.0 V	5.9	6.0	-	V
		I_O = –6.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	V
		I_O = –7.8 mA; V_{CC} = 6.0 V	5.48	5.81	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}				
		I_O = 20 µA; V_{CC} = 2.0 V	-	0	0.1	V
		I_O = 20 µA; V_{CC} = 4.5 V	-	0	0.1	V
		I_O = 20 µA; V_{CC} = 6.0 V	-	0	0.1	V
		I_O = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	V
		I_O = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.26	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.1	µA

Table 6. Static characteristics 74HC366 *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±0.5	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	µA
C_I	input capacitance		-	3.5	-	pF
T_{amb} = −40 °C to +85 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	V
		V_{CC} = 4.5 V	3.15	-	-	V
		V_{CC} = 6.0 V	4.2	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	V
		V_{CC} = 4.5 V	-	-	1.35	V
		V_{CC} = 6.0 V	-	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = −20 µA; V_{CC} = 2.0 V	1.9	-	-	V
		I_O = −20 µA; V_{CC} = 4.5 V	4.4	-	-	V
		I_O = −20 µA; V_{CC} = 6.0 V	5.9	-	-	V
		I_O = −6.0 mA; V_{CC} = 4.5 V	3.84	-	-	V
		I_O = −7.8 mA; V_{CC} = 6.0 V	5.34	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 µA; V_{CC} = 2.0 V	-	-	0.1	V
		I_O = 20 µA; V_{CC} = 4.5 V	-	-	0.1	V
		I_O = 20 µA; V_{CC} = 6.0 V	-	-	0.1	V
		I_O = 6.0 mA; V_{CC} = 4.5 V	-	-	0.33	V
		I_O = 7.8 mA; V_{CC} = 6.0 V	-	-	0.33	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 6.0 V;	-	-	±1.0	µA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±5.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	80	µA
T_{amb} = −40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	V
		V_{CC} = 4.5 V	3.15	-	-	V
		V_{CC} = 6.0 V	4.2	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	V
		V_{CC} = 4.5 V	-	-	1.35	V
		V_{CC} = 6.0 V	-	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = −20 µA; V_{CC} = 2.0 V	1.9	-	-	V
		I_O = −20 µA; V_{CC} = 4.5 V	4.4	-	-	V
		I_O = −20 µA; V_{CC} = 6.0 V	5.9	-	-	V
		I_O = −6.0 mA; V_{CC} = 4.5 V	3.7	-	-	V
		I_O = −7.8 mA; V_{CC} = 6.0 V	5.2	-	-	V

Table 6. Static characteristics 74HC366 *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 µA; V_{CC} = 2.0 V	-	-	0.1	V
		I_O = 20 µA; V_{CC} = 4.5 V	-	-	0.1	V
		I_O = 20 µA; V_{CC} = 6.0 V	-	-	0.1	V
		I_O = 6.0 mA; V_{CC} = 4.5 V	-	-	0.4	V
		I_O = 7.8 mA; V_{CC} = 6.0 V	-	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±1.0	µA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±10.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	160	µA

Table 7. Static characteristics 74HCT366

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V				
		I_O = –20 µA	4.4	4.5	-	V
		I_O = –6.0 mA	3.98	4.32	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V				
		I_O = 20 µA	-	0	0.1	V
		I_O = 6.0 mA	-	0.16	0.26	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±0.1	µA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND per input pin; other inputs at GND or V_{CC}; I_O = 0 A; V_{CC} = 5.5 V	-	-	±0.5	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	8.0	µA
ΔI_{CC}	additional supply current	$V_I = V_{CC}$ – 2.1 V; other inputs at V_{CC} or GND; I_O = 0 A				
		pins nA	-	100	360	µA
		pin $\overline{OE1}$	-	100	360	µA
		pin $\overline{OE2}$	-	90	320	µA
C_I	input capacitance		-	3.5	-	pF
T_{amb} = –40 °C to +85 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V				
		I_O = –20 µA	4.4	-	-	V
		I_O = –6.0 mA	3.84	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V				
		I_O = 20 µA	-	-	0.1	V
		I_O = 6.0 mA	-	-	0.33	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±1.0	µA

Table 7. Static characteristics 74HCT366 *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND per input pin; other inputs at GND or V_{CC}; $I_O = 0$ A; $V_{CC} = 5.5$ V			±5.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	80	µA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $I_O = 0$ A				
		pins nA	-	-	450	µA
		pin $\overline{OE1}$	-	-	450	µA
		pin $\overline{OE2}$	-	-	400	µA
T_{amb} = –40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	-	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; $V_{CC} = 4.5$ V				
		I_O = –20 µA	4.4	-	-	V
		I_O = –6.0 mA	3.7	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; $V_{CC} = 4.5$ V				
		I_O = 20 µA	-	-	0.1	V
		I_O = 6.0 mA	-	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	±1.0	µA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND per input pin; other inputs at GND or V_{CC}; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	±10.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	160	µA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $I_O = 0$ A				
		pins nA	-	-	490	µA
		pin $\overline{OE1}$	-	-	490	µA
		pin $\overline{OE2}$	-	-	441	µA

10. Dynamic characteristics

Table 8. Dynamic characteristics 74HC366

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit Figure 8.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T_{amb} = 25 °C							
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]				
		$V_{CC} = 2.0$ V		-	33	100	ns
		$V_{CC} = 4.5$ V		-	12	20	ns
		$V_{CC} = 5$ V; C_L = 15 pF		-	10	-	ns
		$V_{CC} = 6.0$ V		-	10	17	ns
t_{en}	enable time	$\overline{OEn}$ to nY; see Figure 7	[2]				
		$V_{CC} = 2.0$ V		-	44	150	ns
		$V_{CC} = 4.5$ V		-	16	30	ns
		$V_{CC} = 6.0$ V		-	13	26	ns

Table 8. Dynamic characteristics 74HC366 *…continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit Figure 8.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{dis}	disable time	$\overline{OEn}$ to nY; see Figure 7	[3]				
		V_{CC} = 2.0 V		-	55	150	ns
		V_{CC} = 4.5 V		-	20	30	ns
		V_{CC} = 6.0 V		-	16	26	ns
t_t	transition time	see Figure 6	[4]				
		V_{CC} = 2.0 V		-	14	60	ns
		V_{CC} = 4.5 V		-	5	12	ns
		V_{CC} = 6.0 V		-	4	10	ns
C_{PD}	power dissipation capacitance	per buffer; V_I = GND to V_{CC}	[5]	-	30	-	pF
T_{amb} = −40 °C to +85 °C							
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]				
		V_{CC} = 2.0 V		-	-	125	ns
		V_{CC} = 4.5 V		-	-	25	ns
		V_{CC} = 6.0 V		-	-	21	ns
t_{en}	enable time	$\overline{OEn}$ to nY; see Figure 7	[2]				
		V_{CC} = 2.0 V		-	-	190	ns
		V_{CC} = 4.5 V		-	-	38	ns
		V_{CC} = 6.0 V		-	-	33	ns
t_{dis}	disable time	$\overline{OEn}$ to nY; see Figure 7	[3]				
		V_{CC} = 2.0 V		-	-	190	ns
		V_{CC} = 4.5 V		-	-	38	ns
		V_{CC} = 6.0 V		-	-	33	ns
t_t	transition time	see Figure 6	[4]				
		V_{CC} = 2.0 V		-	-	75	ns
		V_{CC} = 4.5 V		-	-	15	ns
		V_{CC} = 6.0 V		-	-	13	ns
T_{amb} = −40 °C to +125 °C							
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]				
		V_{CC} = 2.0 V		-	-	150	ns
		V_{CC} = 4.5 V		-	-	30	ns
		V_{CC} = 6.0 V		-	-	26	ns
t_{en}	enable time	$\overline{OEn}$ to nY; see Figure 7	[2]				
		V_{CC} = 2.0 V		-	-	225	ns
		V_{CC} = 4.5 V		-	-	45	ns
		V_{CC} = 6.0 V		-	-	38	ns
t_{dis}	disable time	$\overline{OEn}$ to nY; see Figure 7	[3]				
		V_{CC} = 2.0 V		-	-	225	ns
		V_{CC} = 4.5 V		-	-	45	ns
		V_{CC} = 6.0 V		-	-	38	ns

Table 8. Dynamic characteristics 74HC366 *…continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit Figure 8.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_t	transition time	see Figure 6	[4]				
		V_{CC} = 2.0 V		-	-	90	ns
		V_{CC} = 4.5 V		-	-	18	ns
		V_{CC} = 6.0 V		-	-	15	ns

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_{en} is the same as t_{PZH} and t_{PZL}.

[3] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

[4] t_t is the same as t_{THL} and t_{TLH}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

Table 9. Dynamic characteristics 74HCT366

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit Figure 8.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T_{amb} = 25 °C							
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]				
		V_{CC} = 4.5 V		-	13	24	ns
		V_{CC} = 5 V; C_L = 15 pF		-	11	-	ns
t_{en}	enable time	$\overline{OE}n$ to nY; V_{CC} = 4.5 V; see Figure 7	[2]	-	16	35	ns
t_{dis}	disable time	$\overline{OE}n$ to nY; V_{CC} = 4.5 V; see Figure 7	[3]	-	20	35	ns
t_t	transition time	V_{CC} = 4.5 V; see Figure 6	[4]	-	5	12	ns
C_{PD}	power dissipation capacitance	per buffer; V_I = GND to (V_{CC} − 1.5 V)	[5]	-	30	-	pF
T_{amb} = −40 °C to +85 °C							
t_{pd}	propagation delay	nA to nY; V_{CC} = 4.5 V; see Figure 6	[1]	-	-	30	ns
t_{en}	enable time	$\overline{OE}n$ to nY; V_{CC} = 4.5 V; see Figure 7	[2]	-	-	44	ns
t_{dis}	disable time	$\overline{OE}n$ to nY; V_{CC} = 4.5 V; see Figure 7	[3]	-	-	44	ns
t_t	transition time	V_{CC} = 4.5 V; see Figure 6	[4]	-	-	15	ns
T_{amb} = −40 °C to +125 °C							
t_{pd}	propagation delay	nA to nY; V_{CC} = 4.5 V; see Figure 6	[1]	-	-	36	ns
t_{en}	enable time	$\overline{OE}n$ to nY; V_{CC} = 4.5 V; see Figure 7	[2]	-	-	53	ns
t_{dis}	disable time	$\overline{OE}n$ to nY; V_{CC} = 4.5 V; see Figure 7	[3]	-	-	53	ns
t_t	transition time	V_{CC} = 4.5 V; see Figure 6	[4]	-	-	18	ns

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

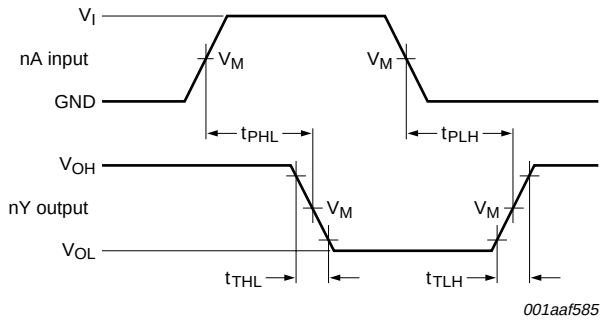
[2] t_{en} is the same as t_{PZH} and t_{PZL}.

[3] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

[4] t_t is the same as t_{THL} and t_{TLH}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

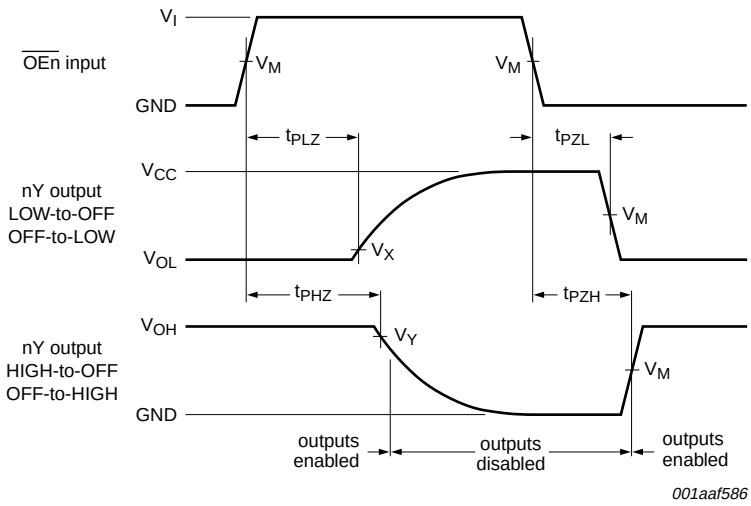
11. Waveforms



Measurement points are given in Table 10.

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 6. Propagation delay data input (nA) to output (nY) and output transition time



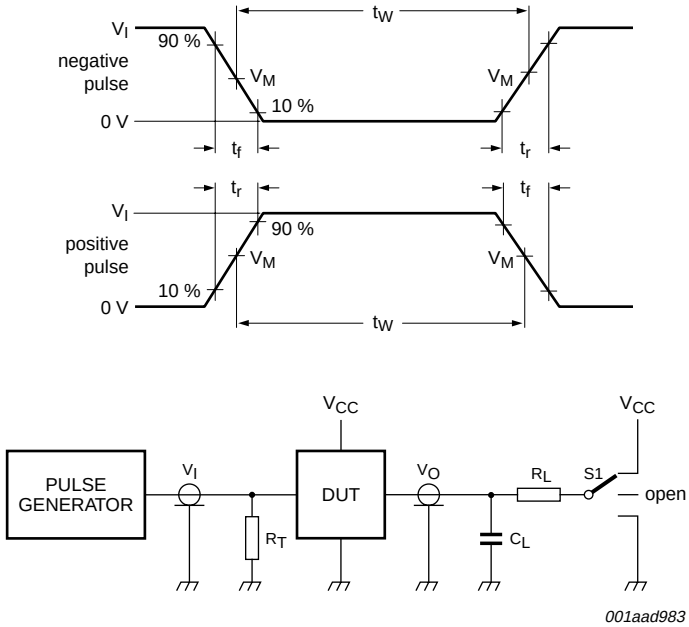
Measurement points are given in Table 10.

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 7. 3-state enable and disable times

Table 10. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC366	$0.5V_{CC}$	$0.5V_{CC}$	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$
74HCT366	1.3 V	1.3 V	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$



Test data is given in Table 11.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistor

S1 = Test selection switch

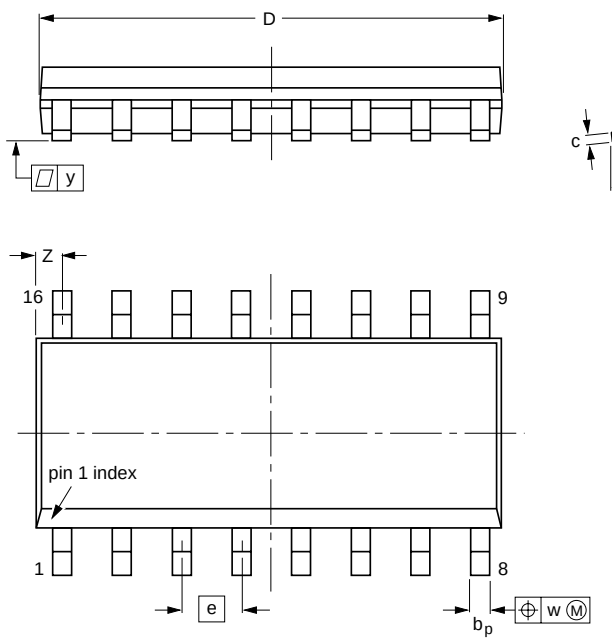
Fig 8. Load circuitry for measuring switching times

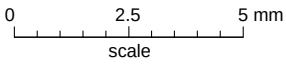
Table 11. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC366	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}
74HCT366	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**





DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

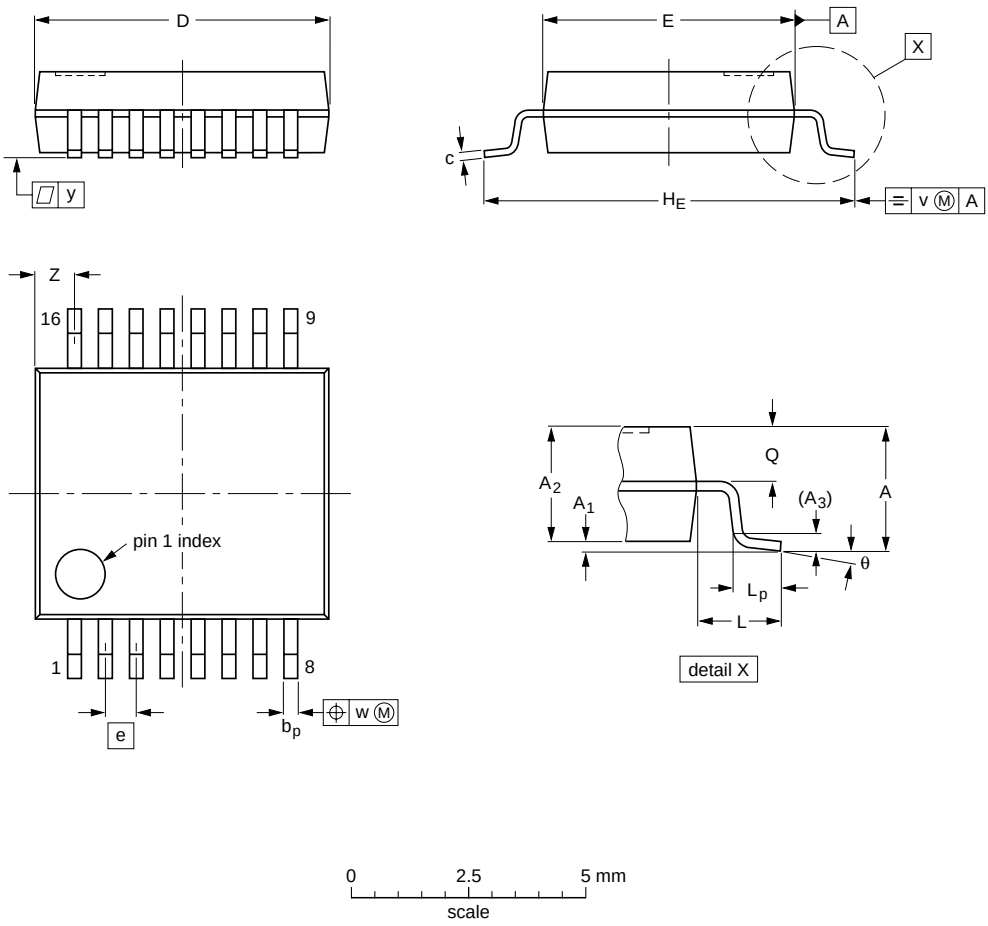
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm **SOT338-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8^o 0^o

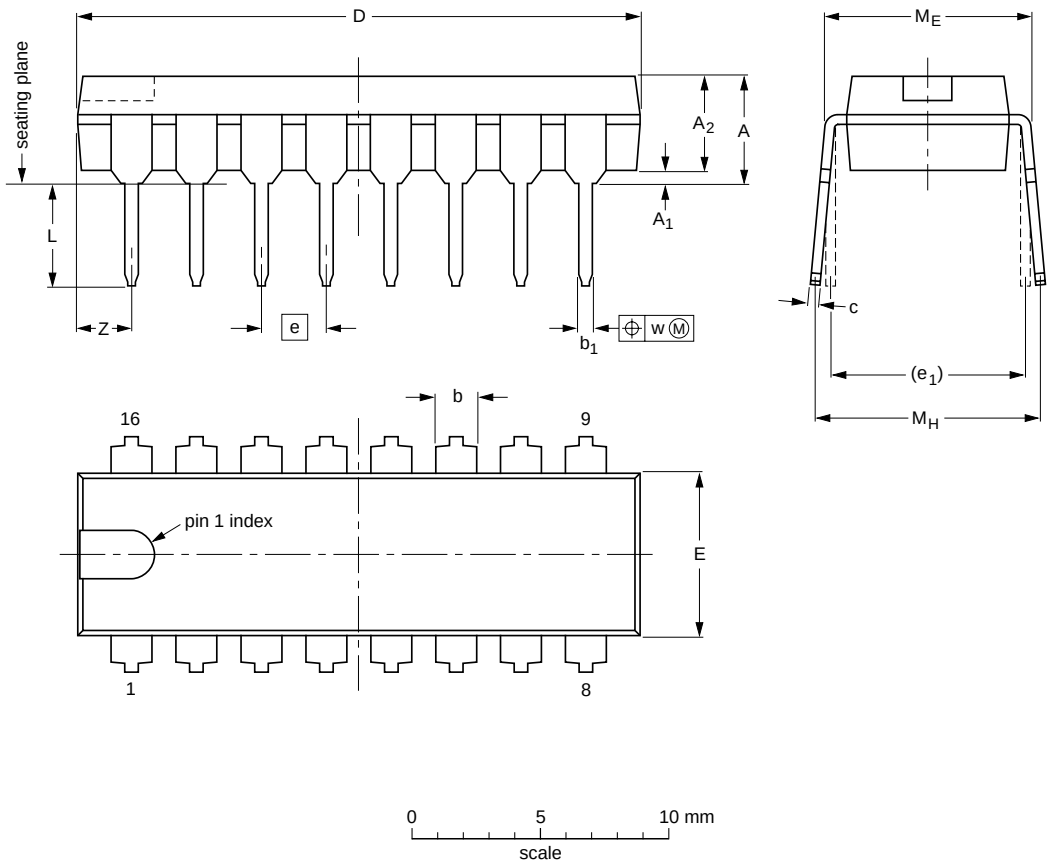
Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT338-1		MO-150				~~99-12-27~~ 03-02-19

Fig 10. Package outline SOT338-1 (SSOP16)

DIP16: plastic dual in-line package; 16 leads (300 mil); long body **SOT38-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1 min.	A_2 max.	b	b_1	c	D (1)	E (1)	e	e_1	L	M_E	M_H	w	Z (1) max.
mm	4.7	0.51	3.7	1.40 1.14	0.53 0.38	0.32 0.23	21.8 21.4	6.48 6.20	2.54	7.62	3.9 3.4	8.25 7.80	9.5 8.3	0.254	2.2
inches	0.19	0.02	0.15	0.055 0.045	0.021 0.015	0.013 0.009	0.86 0.84	0.26 0.24	0.1	0.3	0.15 0.13	0.32 0.31	0.37 0.33	0.01	0.087

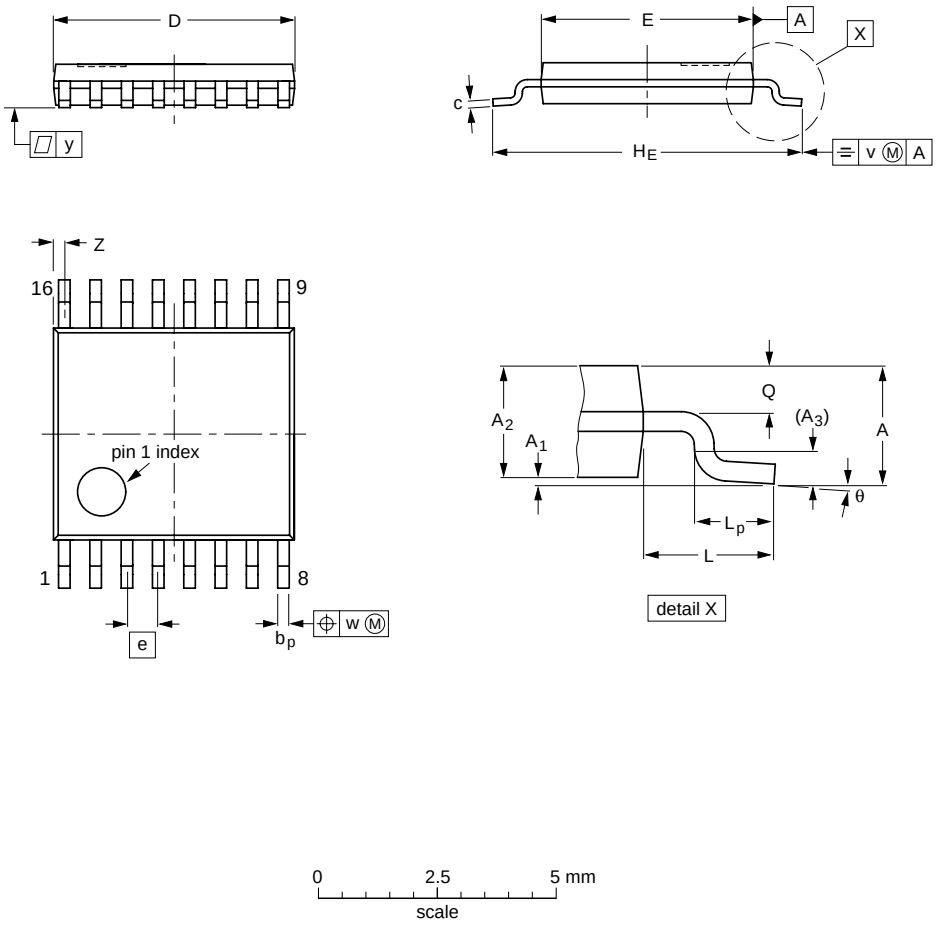
Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-1	050G09	MO-001	SC-503-16			~~99-12-27~~ 03-02-13

Fig 11. Package outline SOT38-1 (DIP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 12. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT366_3	20061121	Product data sheet	-	74HC_HCT366_CNV_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors • Legal texts have been adapted to the new company name where appropriate • Added family specification			
74HC_HCT366_CNV_2	19901201	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

15.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contact information

For additional information, please visit: **http://www.nxp.com**

For sales office addresses, send an email to: **salesaddresses@nxp.com**

17. Contents

For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 21 November 2006

Document identifier: 74HC_HCT366_3